

RF Power Field Effect Transistors

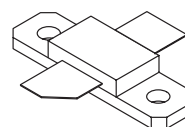
N-Channel Enhancement-Mode Lateral MOSFETs

Designed for broadband commercial and industrial applications with frequencies up to 1000 MHz. The high gain and broadband performance of these devices make them ideal for large-signal, common-source amplifier applications in 26 volt base station equipment.

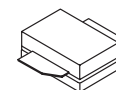
- Typical Two-Tone Performance at 945 MHz, 26 Volts
 - Output Power — 60 Watts PEP
 - Power Gain — 17 dB
 - Efficiency — 40%
 - IMD — -31 dBc
- Integrated ESD Protection
- Designed for Maximum Gain and Insertion Phase Flatness
- Capable of Handling 10:1 VSWR, @ 26 Vdc, 945 MHz, 60 Watts CW Output Power
- Excellent Thermal Stability
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- In Tape and Reel. R1 Suffix = 500 Units per 32 mm, 13 inch Reel.
- Low Gold Plating Thickness on Leads. L Suffix Indicates 40μ" Nominal.

MRF9060LR1
MRF9060LSR1

945 MHz, 60 W, 26 V
LATERAL N-CHANNEL
BROADBAND
RF POWER MOSFETs



CASE 360B-05, STYLE 1
NI-360
MRF9060LR1



CASE 360C-05, STYLE 1
NI-360S
MRF9060LSR1

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-0.5, +65	Vdc
Gate-Source Voltage	V _{GS}	-0.5, +15	Vdc
Total Device Dissipation @ T _C = 25°C	P _D	159	W
Derate above 25°C		0.91	W/°C
		219	W
		1.25	W/°C
Storage Temperature Range	T _{stg}	-65 to +150	°C
Operating Junction Temperature	T _J	200	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case	R _{θJC}	1.1	°C/W
		0.8	

Table 3. ESD Protection Characteristics

Test Conditions	Class
Human Body Model	1 (Minimum)
Machine Model	M1 (Minimum)

NOTE – CAUTION – MOS devices are susceptible to damage from electrostatic charge. Reasonable precautions in handling and packaging MOS devices should be observed.

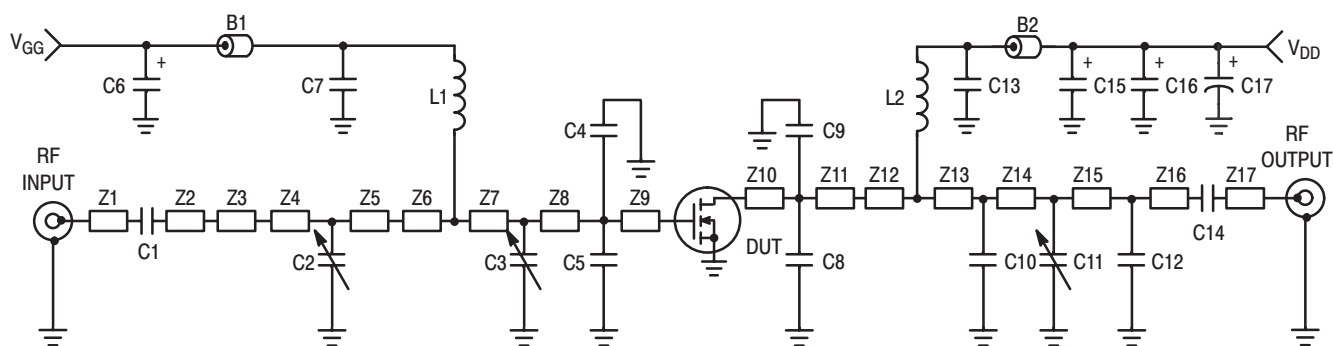
Table 4. Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Off Characteristics					
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 65\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	10	μAdc
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 26\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	1	μAdc
Gate–Source Leakage Current ($V_{GS} = 5\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}	—	—	1	μAdc
On Characteristics					
Gate Threshold Voltage ($V_{DS} = 10\text{ Vdc}$, $I_D = 200\text{ }\mu\text{Adc}$)	$V_{GS(th)}$	2	2.9	4	Vdc
Gate Quiescent Voltage ($V_{DS} = 26\text{ Vdc}$, $I_D = 450\text{ mAdc}$)	$V_{GS(Q)}$	—	3.7	—	Vdc
Drain–Source On–Voltage ($V_{GS} = 10\text{ Vdc}$, $I_D = 1.3\text{ Adc}$)	$V_{DS(on)}$	—	0.17	0.4	Vdc
Forward Transconductance ($V_{DS} = 10\text{ Vdc}$, $I_D = 4\text{ Adc}$)	g_{fs}	—	5.3	—	S
Dynamic Characteristics					
Input Capacitance ($V_{DS} = 26\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{iss}	—	98	—	pF
Output Capacitance ($V_{DS} = 26\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{oss}	—	50	—	pF
Reverse Transfer Capacitance ($V_{DS} = 26\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{rss}	—	2	—	pF

(continued)

Table 4. Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted) (continued)

Characteristic	Symbol	Min	Typ	Max	Unit
Functional Tests (In Freescale Test Fixture, 50 ohm system)					
Two-Tone Common-Source Amplifier Power Gain ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 60\text{ W PEP}$, $I_{DQ} = 450\text{ mA}$, $f_1 = 945.0\text{ MHz}$, $f_2 = 945.1\text{ MHz}$)	G_{ps}	16	17	—	dB
Two-Tone Drain Efficiency ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 60\text{ W PEP}$, $I_{DQ} = 450\text{ mA}$, $f_1 = 945.0\text{ MHz}$, $f_2 = 945.1\text{ MHz}$)	η	36	40	—	%
3rd Order Intermodulation Distortion ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 60\text{ W PEP}$, $I_{DQ} = 450\text{ mA}$, $f_1 = 945.0\text{ MHz}$, $f_2 = 945.1\text{ MHz}$)	IMD	—	-31	-28	dBc
Input Return Loss ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 60\text{ W PEP}$, $I_{DQ} = 450\text{ mA}$, $f_1 = 945.0\text{ MHz}$, $f_2 = 945.1\text{ MHz}$)	IRL	—	-16	-9	dB
Two-Tone Common-Source Amplifier Power Gain ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 60\text{ W PEP}$, $I_{DQ} = 450\text{ mA}$, $f_1 = 930.0\text{ MHz}$, $f_2 = 930.1\text{ MHz}$ and $f_1 = 960.0\text{ MHz}$, $f_2 = 960.1\text{ MHz}$)	G_{ps}	—	17	—	dB
Two-Tone Drain Efficiency ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 60\text{ W PEP}$, $I_{DQ} = 450\text{ mA}$, $f_1 = 930.0\text{ MHz}$, $f_2 = 930.1\text{ MHz}$ and $f_1 = 960.0\text{ MHz}$, $f_2 = 960.1\text{ MHz}$)	η	—	39	—	%
3rd Order Intermodulation Distortion ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 60\text{ W PEP}$, $I_{DQ} = 450\text{ mA}$, $f_1 = 930.0\text{ MHz}$, $f_2 = 930.1\text{ MHz}$ and $f_1 = 960.0\text{ MHz}$, $f_2 = 960.1\text{ MHz}$)	IMD	—	-31	—	dBc
Input Return Loss ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 60\text{ W PEP}$, $I_{DQ} = 450\text{ mA}$, $f_1 = 930.0\text{ MHz}$, $f_2 = 930.1\text{ MHz}$ and $f_1 = 960.0\text{ MHz}$, $f_2 = 960.1\text{ MHz}$)	IRL	—	-16	—	dB
Power Output, 1 dB Compression Point ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 60\text{ W CW}$, $I_{DQ} = 450\text{ mA}$, $f_1 = 945.0\text{ MHz}$)	P_{1dB}	—	70	—	W
Common-Source Amplifier Power Gain ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 60\text{ W CW}$, $I_{DQ} = 450\text{ mA}$, $f_1 = 945.0\text{ MHz}$)	G_{ps}	—	17	—	dB
Drain Efficiency ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 60\text{ W CW}$, $I_{DQ} = 450\text{ mA}$, $f_1 = 945.0\text{ MHz}$)	η	—	51	—	%
Output Mismatch Stress ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 60\text{ W CW}$, $I_{DQ} = 450\text{ mA}$, $f = 945.0\text{ MHz}$, VSWR = 10:1, All Phase Angles at Frequency of Tests)	Ψ	No Degradation In Output Power			

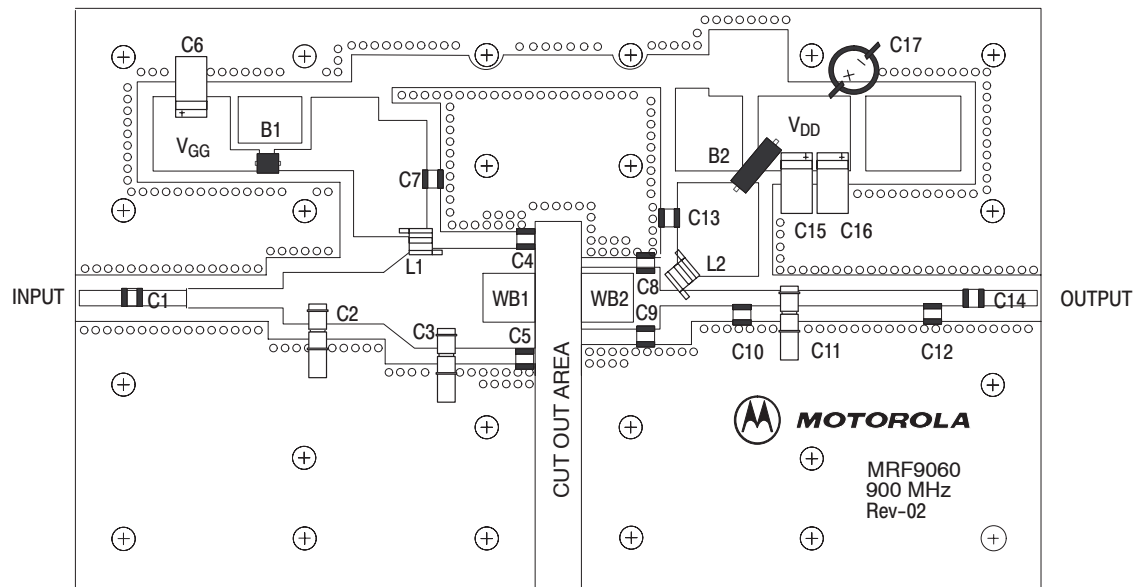


Z1	0.240" x 0.060" Microstrip	Z10	0.360" x 0.270" Microstrip
Z2	0.240" x 0.060" Microstrip	Z11	0.060" x 0.270" Microstrip
Z3	0.500" x 0.100" Microstrip	Z12	0.110" x 0.060" Microstrip
Z4	0.180" x 0.270" Microstrip	Z13	0.330" x 0.060" Microstrip
Z5	0.350" x 0.270" Microstrip	Z14	0.230" x 0.060" Microstrip
Z6	0.270" x 0.520 x 0.140" Taper	Z15	0.740" x 0.060" Microstrip
Z7	0.170" x 0.520" Microstrip	Z16	0.130" x 0.060" Microstrip
Z8	0.410" x 0.520" Microstrip	Z17	0.340" x 0.060" Microstrip
Z9	0.060" x 0.520" Microstrip	PCB	Taconic RF-35-0300, 30 mil, $\epsilon_r = 3.55$

Figure 1. 945 MHz Broadband Test Circuit Schematic

Table 5. 945 MHz Broadband Test Circuit Component Designations and Values

Part	Description	Part Number	Manufacturer
B1	Short Ferrite Bead	95F786	Newark
B2	Long Ferrite Bead	95F787	Newark
C1, C7, C13, C14	47 pF Chip Capacitors	100B470JP 500X	ATC
C2, C3, C11	0.8–8.0 Gigatrim Variable Capacitors	44F3360	Newark
C4, C5, C8, C9	10 pF Chip Capacitors	100B100JP 500X	ATC
C6, C15, C16	10 μ F, 35 V Tantalum Chip Capacitor	93F2975	Newark
C10	3.0 pF Chip Capacitor	100B3R0JP 500X	ATC
C12	0.5 pF Chip Capacitor (MRF9060) 0.7 pF Chip Capacitor (MRF9060S)	100B0R5BP 500X 100B0R7BP 500X	ATC ATC
C17	220 μ F Electrolytic Chip Capacitor	14F185	Newark
L1, L2	12.5 nH Inductors	A04T-5	Coilcraft
N1, N2	N-Type Panel Mount, Stripline	3052-1648-10	Avnet
WB1, WB2	10 mil Brass Wear Blocks		



Freescall has begun the transition of marking Printed Circuit Boards (PCBs) with the Freescall Semiconductor signature/logo. PCBs may have either Motorola or Freescall markings during the transition period. These changes will have no impact on form, fit or function of the current product.

Figure 2. 930 – 960 MHz Broadband Test Circuit Component Layout

TYPICAL CHARACTERISTICS

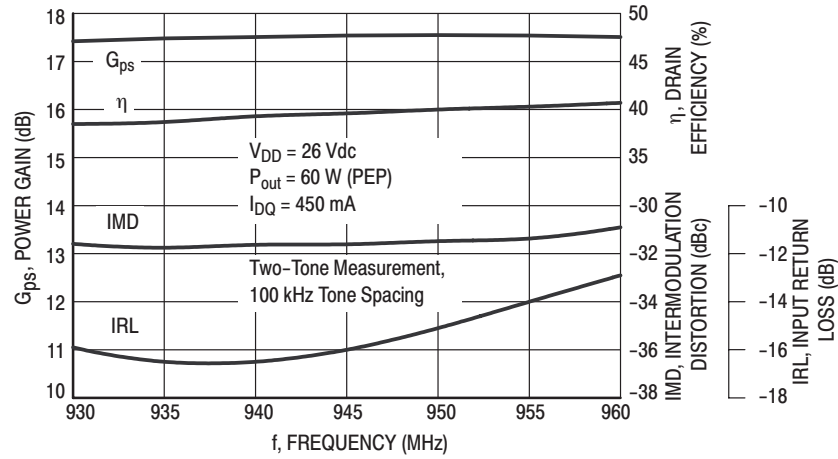


Figure 3. Class AB Broadband Circuit Performance

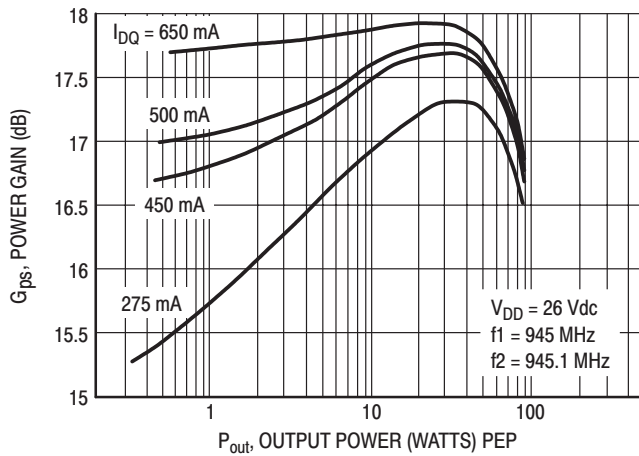


Figure 4. Power Gain versus Output Power

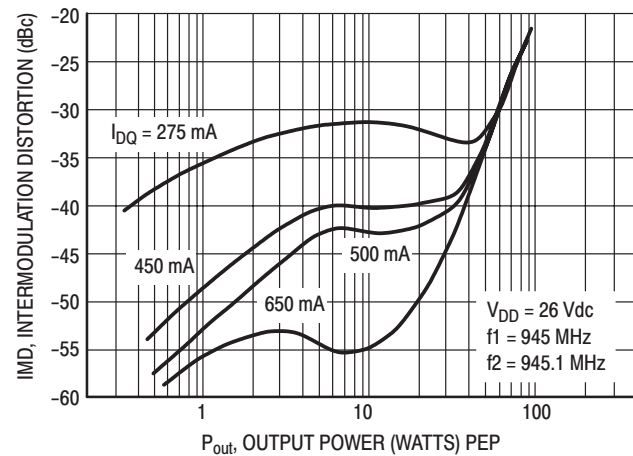


Figure 5. Intermodulation Distortion versus Output Power

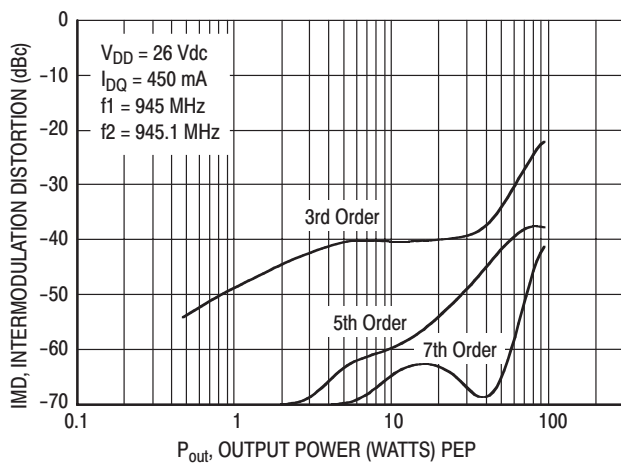


Figure 6. Intermodulation Distortion Products versus Output Power

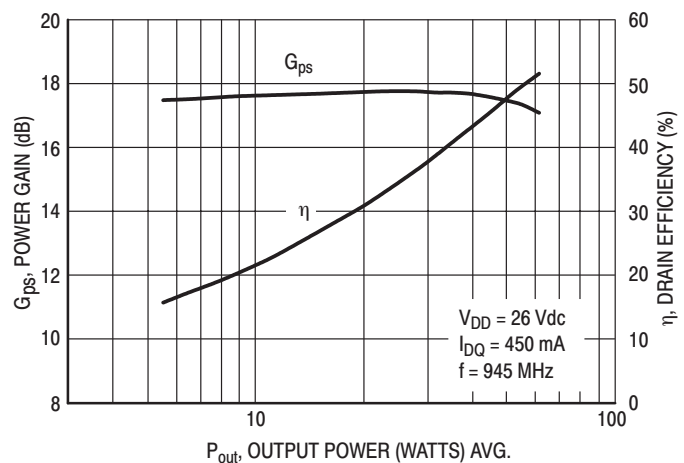


Figure 7. Power Gain and Efficiency versus Output Power

TYPICAL CHARACTERISTICS

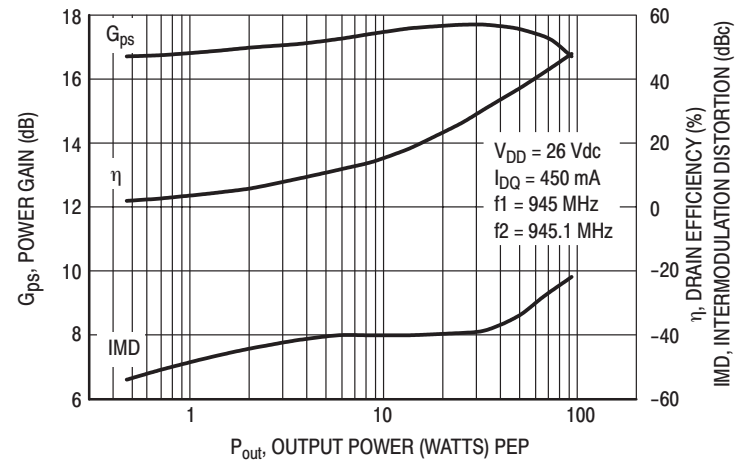
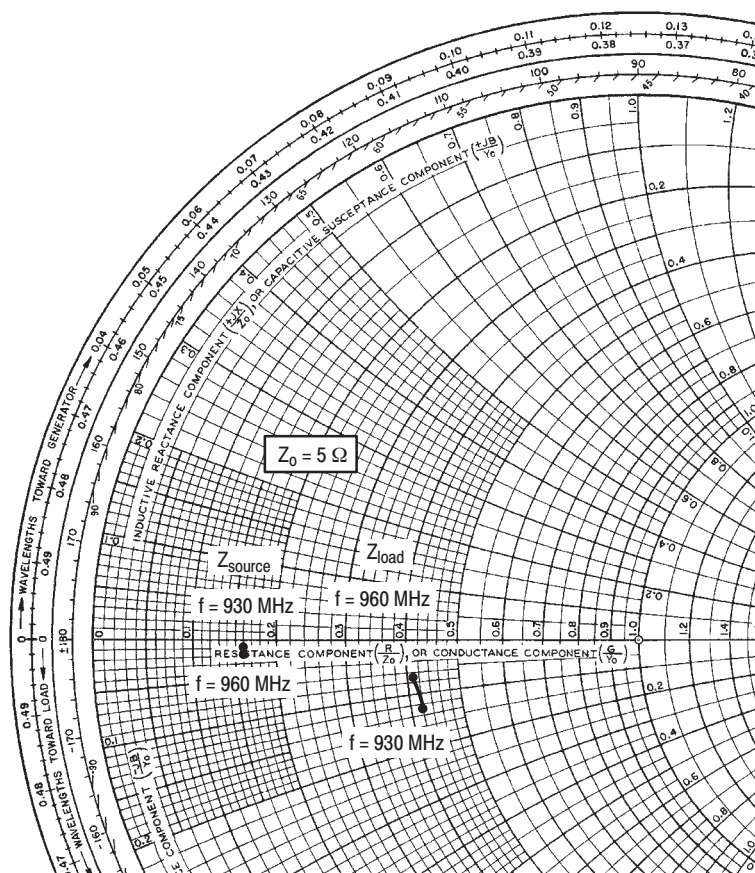


Figure 8. Power Gain, Efficiency, and IMD versus Output Power



$V_{DD} = 26\text{ V}$, $I_{DQ} = 450\text{ mA}$, $P_{out} = 60\text{ W PEP}$

f MHz	Z_{source} Ω	Z_{load} Ω
930	$0.80 - j0.10$	$2.08 - j0.65$
945	$0.80 - j0.05$	$2.07 - j0.38$
960	$0.81 - j0.10$	$2.04 - j0.37$

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

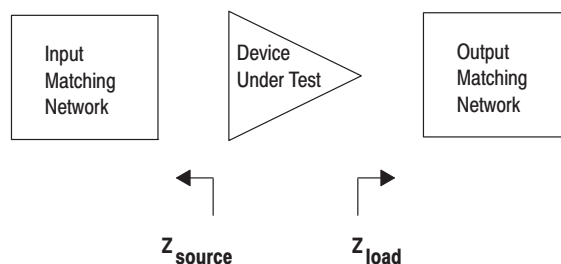
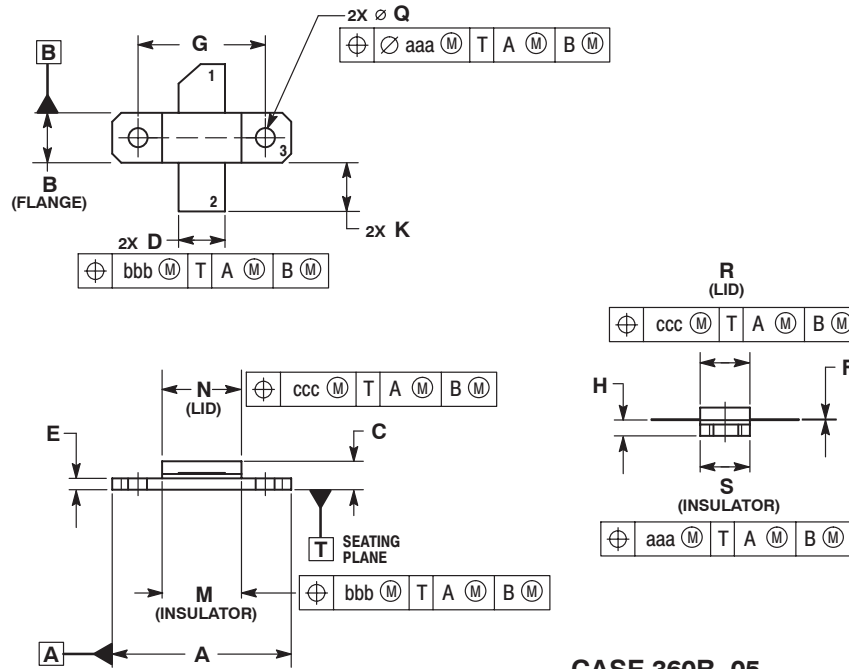


Figure 9. Series Equivalent Source and Load Impedance

NOTES

NOTES

PACKAGE DIMENSIONS

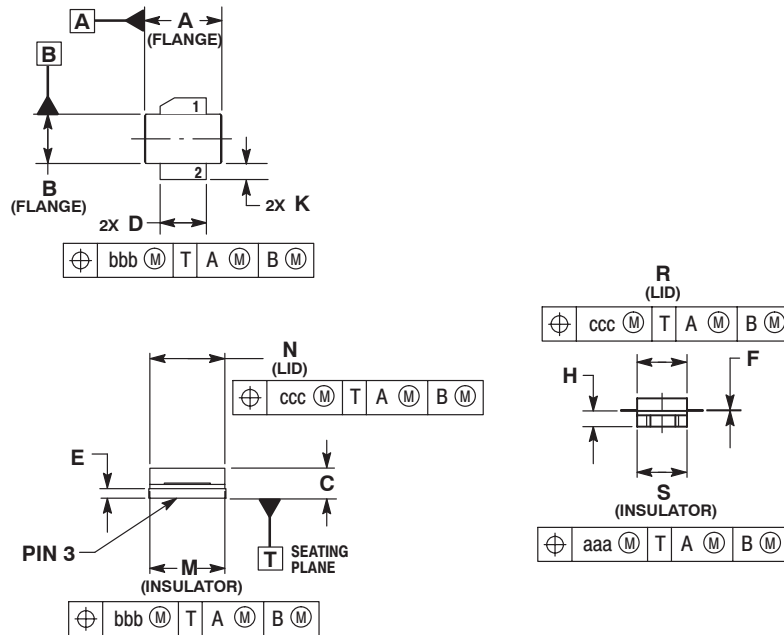


- NOTES:
1. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.795	0.805	20.19	20.45
B	0.225	0.235	5.72	5.97
C	0.125	0.175	3.18	4.45
D	0.210	0.220	5.33	5.59
E	0.055	0.065	1.40	1.65
F	0.004	0.006	0.10	0.15
G	0.562 BSC		14.28 BSC	
H	0.077	0.087	1.96	2.21
K	0.220	0.250	5.59	6.35
M	0.355	0.365	9.02	9.27
N	0.357	0.363	9.07	9.22
Q	0.125	0.135	3.18	3.43
R	0.227	0.233	5.77	5.92
S	0.225	0.235	5.72	5.97
aaa	0.005 REF		0.13 REF	
bbb	0.010 REF		0.25 REF	
ccc	0.015 REF		0.38 REF	

STYLE 1:
PIN 1. DRAIN
2. GATE
3. SOURCE

**CASE 360B-05
ISSUE F
NI-360
MRF9060LR1**



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 3. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.375	0.385	9.53	9.78
B	0.225	0.235	5.72	5.97
C	0.105	0.155	2.67	3.94
D	0.210	0.220	5.33	5.59
E	0.035	0.045	0.89	1.14
F	0.004	0.006	0.10	0.15
H	0.057	0.067	1.45	1.70
K	0.085	0.115	2.16	2.92
M	0.355	0.365	9.02	9.27
N	0.357	0.363	9.07	9.22
R	0.227	0.23	5.77	5.92
S	0.225	0.235	5.72	5.97
aaa	0.005 REF		0.13 REF	
bbb	0.010 REF		0.25 REF	
ccc	0.015 REF		0.38 REF	

STYLE 1:
PIN 1. DRAIN
2. GATE
3. SOURCE

**CASE 360C-05
ISSUE D
NI-360S
MRF9060LSR1**

MRF9060LR1 MRF9060LSR1

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